Electronic Supplementary Material (ESI) for RSC Advances.

Bistable electrical switching and nonvolatile memory effect by doping different content of GO in Poly (9,9-dioctylfluorene-2,7-diyl)

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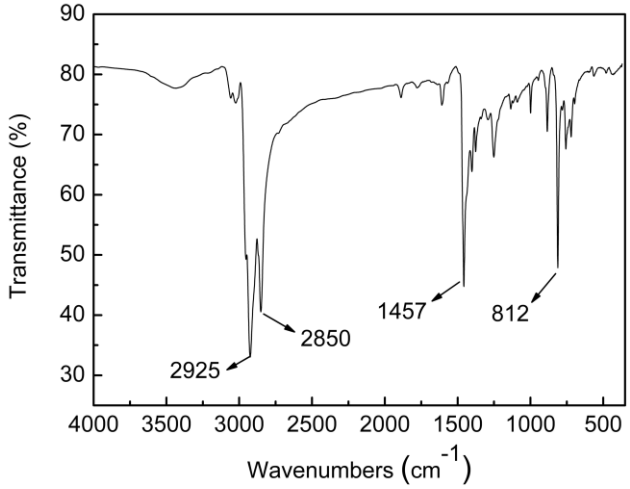

Figure S1 The FT-IR spectra of PFO

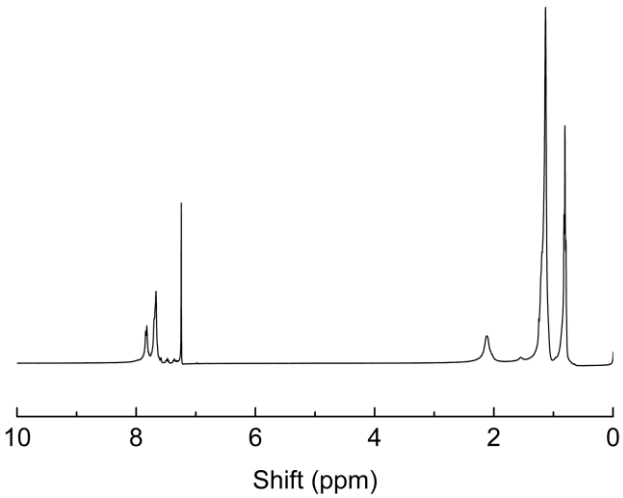

Figure S2 ^{1}H spectra of PFO in $CDCl_3$

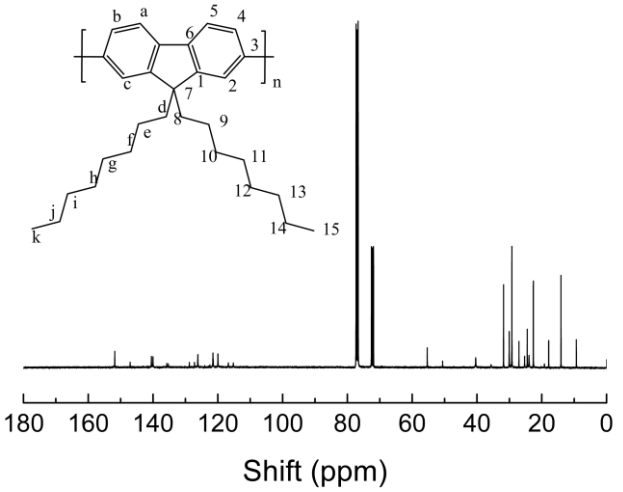

Figure S3 ^{13}C NMR spectra of PFO in $CDCl_3$